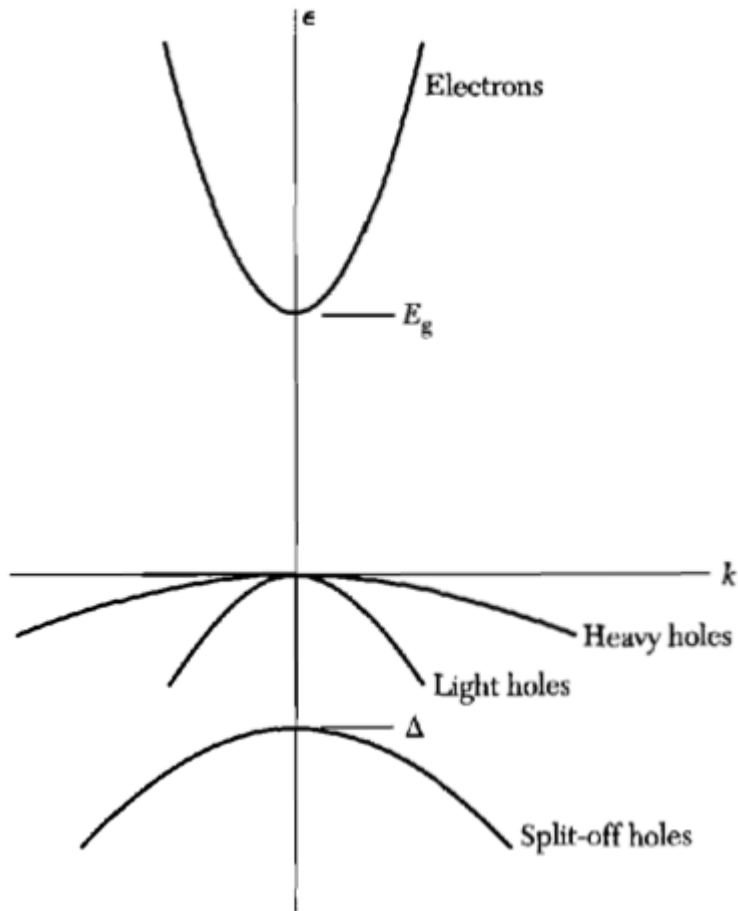


PHY404- Solid State Physics II

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Band edge structure



At the center of the Brillouin zone (is defined as a Wigner-Seitz primitive cell in the reciprocal lattice), the band structure for direct-gap semiconductors is given in the figure.

Simplified view of the band edge structure of a direct-gap semiconductor

Band edge structure

The conduction band edge is spherical with the effective mass m_0 :

$$\epsilon_c = E_g + \hbar^2 k^2 / 2m_e$$

The valence bands are characteristically threefold near the edge, with the heavy hole hh and light hole lh bands degenerate at the center, and a band soh split off by the spin-orbit splitting Δ :

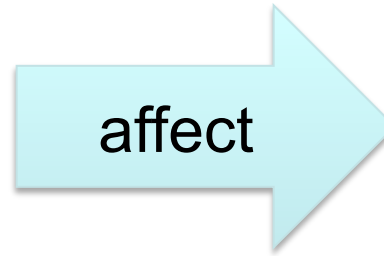
$$\begin{aligned} \epsilon_v(hh) &\cong -\hbar^2 k^2 / 2m_{hh} ; & \epsilon_v(lh) &\cong -\hbar^2 k^2 / 2m_{lh} ; \\ \epsilon_v(soh) &\cong -\Delta - \hbar^2 k^2 / 2m_{soh} . \end{aligned}$$

Band edge structure

The perturbation theory of band edges suggests that the electron effective mass should be proportional to the band gap, approximately, for a direct gap crystal.

Impurity Conductivity

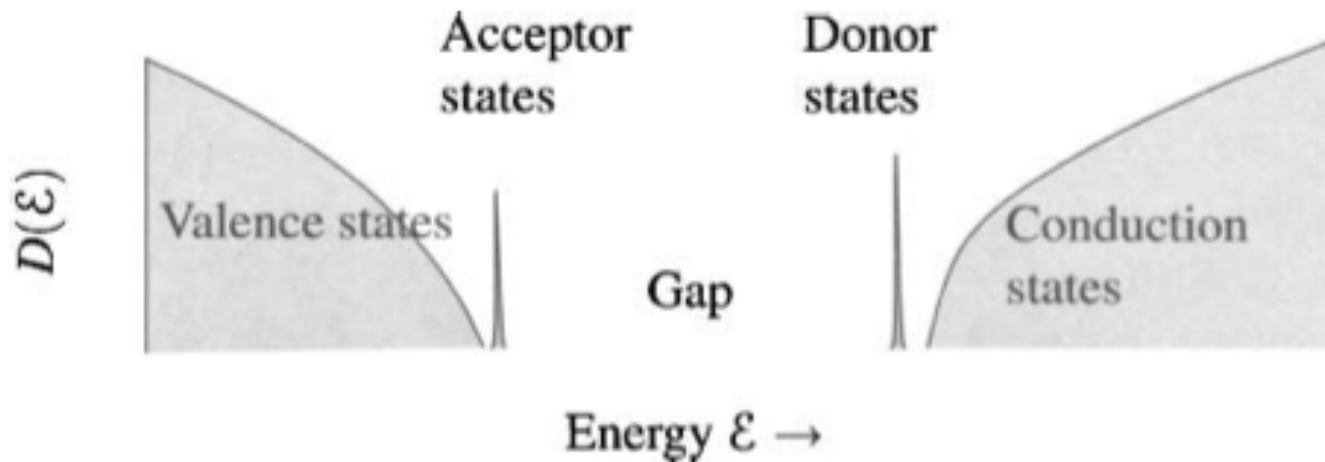
- **Impurities**
- **Imperfections**



**The electrical
properties of
semiconductor**

Extrinsic Semiconductor

- The effect of adding donors to a semiconductor is to create a population of bound states sitting just below the conduction band, while adding acceptors creates bound states just above the valence band.



Extrinsic Semiconductor

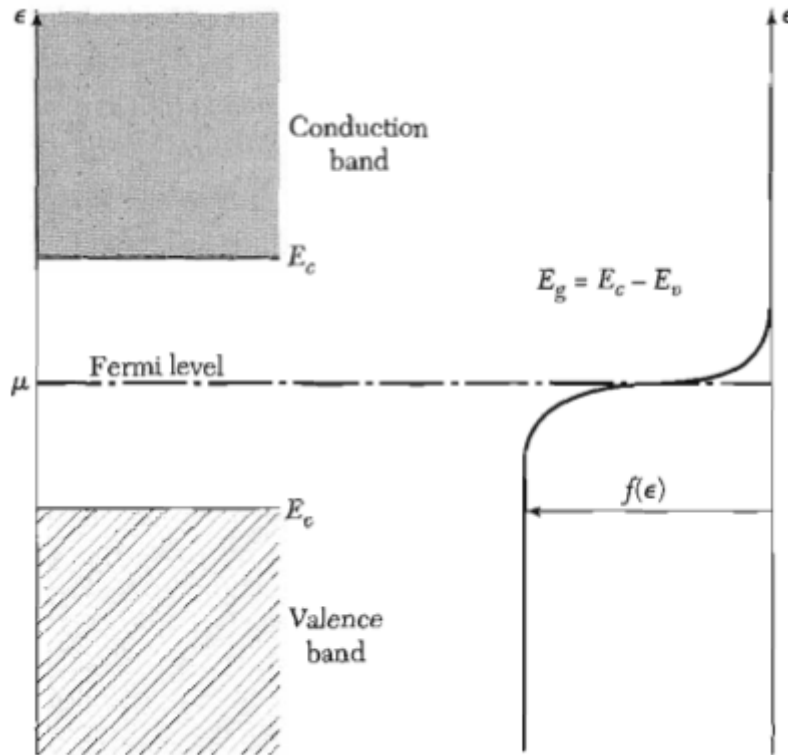
- At room temperature, almost all the bound states break apart; each donor gives an electron to the conduction band, while each acceptor gives a hole to the valence band.
- When certain sorts of impurities are used to dope a semiconductor, the physics changes rather dramatically

Extrinsic Semiconductor

- The most interesting impurities are noncompensated, lying one column to the right or one column to the left of a semiconductor in the periodic table.

Intrinsic Semiconductor

- Concentration of intrinsic carriers as a function of temperature



Energy scale for statistical calculations.